

PTO/SB/08a/b (08-03)

Approved for use through 07/31/2008. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/B/PTO				Complete If Known	
				Application Number	10/618,824-Conf. #5907
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A- 2f23
				Examiner Name	Not Yet Assigned H. Lee
Sheet	1	of	1	Attorney Docket Number	M4065.1006/P1006-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
<i>Lee</i>	AA	US-6,337,266	01/08/2002	Zahorik	

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
					T ⁶

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

Hsin Ming Lee 6/16/04



Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

Complete if Known

Application Number	10/618,824
Filing Date	July 14, 2003
First Named Inventor	Terry L. Gilton
Art Unit	N/A 2723
Examiner Name	Not Yet Assigned H. Lee

Sheet

1

of

12

Attorney Docket Number

M4065.1006/P1006-A

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
Lee	AA	2002/0000666	1/2002	Kozicki et al.	
Lee	AB	2002/0072188	6/2002	Gilton	
*	AC	2002/0106849	08/2002	Moore	
*	AD	2002/0123169	09/2002	Moore et al.	
*	AE	2002/0123170	09/2002	Moore et al.	
*	AF	2002/0123248	09/2002	Moore et al.	
*	AG	2002/0127886	09/2002	Moore et al.	
*	AH	2002/0132417	09/2002	Li	
*	AI	2002/0160551	10/2002	Harshfield	
*	AJ	2002/0163828	11/2002	Krieger et al.	
*	AK	2002/0168852	11/2002	Harshfield et al.	
*	AL	2002/0190289	12/2002	Harshfield et al.	
*	AM	2003/0001229	01/2003	Moore et al.	
*	AN	2003/0027416	02/2003	Moore	
*	AO	2003/0032254	02/2003	Gilton	
*	AP	2003/0038301	02/2003	Moore	
*	AQ	2003/0043631	03/2003	Gilton et al.	
*	AR	2003/0045049	03/2003	Campbell et al.	
*	AS	2003/0045054	03/2003	Campbell et al.	
*	AT	2003/0047765	03/2003	Campbell	
*	AU	2003/0047772	03/2003	Li	
*	AV	2003/0047773	03/2003	Li	
*	AW	2003/0049912	03/2003	Campbell et al.	
*	AX	2003/0068861	04/2003	Li	
*	AY	2003/0068862	04/2003	Li	
*	AZ	2003/0095426	05/2003	Hush et al.	
*	AA1	2003/0096497	05/2003	Moore et al.	
*	AB1	2003/0107105	06/2003	Kozicki	
*	AC1	2003/0117831	06/2003	Hush	
*	AD1	2003/0128612	07/2003	Moore et al.	
*	AE1	2003/0137869	07/2003	Kozicki	
*	AF1	2003/0143782	07/2003	Gilton et al.	
*	AG1	2003/0155589	08/2003	Campbell et al.	
*	AH1	2003/0155606	08/2003	Campbell et al.	
*	AI1	2003/0156447	08/2003	Kozicki	
*	AJ1	2003/0156463	08/2003	Casper et al.	
*	AK1	2003/0209728	11/2003	Kozicki et al	
*	AL1	2003/0209971	11/2003	Kozicki et al	
*	AM1	2003/0210564	11/2003	Kozicki et al	
*	AN1	3,622,319	11/1971	Sharp	
*	AO1	3,743,847	7/1973	Boland	
*	AP1	4,269,935	5/1981	Masters et al.	
*	AQ1	4,312,938	1/1982	Drexler, et al.	
*	AR1	4,316,946	1/1982	Masters, et al.	

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

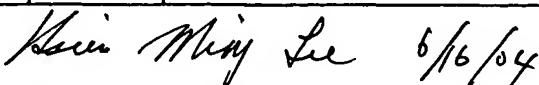
Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

				<i>Complete if Known</i>
Sheet		2	of	12
				Attorney Docket Number
				M4065.1006/P1006-A

✓ 22	AS1	4,320,191	3/1982	Yoshikawa et al.
•	AT1	4,405,710	9/1983	Balasubramanyam et al.
•	AU1	4,419,421	12/1983	Wichelhaus, et al.
•	AV1	4,499,557	2/1985	Holmberg et al.
•	AW1	4,671,618	06/1987	Wu et al.
•	AX1	4,795,657	1/1989	Formigoni et al.
•	AY1	4,800,526	01/1989	Lewis
•	AZ1	4,847,674	7/1989	Sliwa et al.
•	AA2	5,177,567	1/1993	Klersy et al.
•	AB2	5,219,788	6/1993	Abernathey et al.
•	AC2	5,238,862	8/1993	Blalock et al.
•	AD2	5,272,359	12/1993	Nagasubramanian et al.
•	AE2	5,314,772	5/1994	Kozicki
•	AF2	5,315,131	5/1994	Kishimoto et al.
•	AG2	5,350,484	9/1994	Gardner et al.
•	AH2	5,360,981	11/1994	Owen et al.
•	AI2	5,500,532	3/1996	Kozicki et al.
•	AJ2	5,512,328	4/1996	Yoshimura et al.
•	AK2	5,512,773	4/1996	Wolf et al.
•	AL2	5,726,083	3/1998	Takaishi
•	AM2	5,751,012	5/1998	Wolstenholme et al.
•	AN2	5,789,277	8/1998	Zahorik et al.
•	AO2	5,814,527	9/1998	Wolstenholme et al
•	AP2	5,818,749	10/1998	Harshfield
•	AQ2	5,841,150	11/1998	Gonzalez et al.
•	AR2	5,846,889	12/1998	Harbison et al.
•	AS2	5,851,882	12/1998	Harshfield
•	AT2	5,869,843	2/1999	Harshfield
•	AU2	5,920,788	7/1999	Reinberg
•	AV2	5,998,066	12/1999	Block et al.
•	AW2	6,031,287	2/2000	Harshfield
•	AX2	6,072,716	6/2000	Jacobson et al.
•	AY2	6,077,729	6/2000	Harshfield
•	AZ2	6,177,338	1/2001	Liaw et al.
•	AA3	6,117,720	9/2000	Harshfield
•	AB3	6,143,604	11/2000	Chiang et al.
•	AC3	6,236,059	5/2001	Wolstenholme et al.
•	AD3	6,297,170	10/2001	Gabriel et al.
•	AE3	6,300,684	10/2001	Gonzalez et al.
•	AF3	6,316,784	11/2001	Zahorik et al.
•	AG3	6,329,606	12/2001	Freyman et al.
•	AH3	6,350,679	2/2002	McDaniel et al.
•	AI3	6,376,284	4/2002	Gonzalez et al.
•	AJ3	6,388,324	5/2002	Kozicki et al.
•	AK3	6,391,688	5/2002	Gonzalez et al.
•	AL3	6,414,376	7/2002	Thakur et al.
•	AM3	6,418,049	7/2002	Kozicki et al.
•	AN3	6,420,725	7/2002	Harshfield
✓ 23	AO3	6,423,628	7/2002	Li et al.


Karen May Lee
6/6/04

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/618,824
(use as many sheets as necessary)				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A- 2823
				Examiner Name	Not Yet Assigned H Lee
Sheet	3	of	12	Attorney Docket Number M4065.1006/P1006-A	

Karen Meng Lee 6/16/04

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				<i>Complete if Known</i>	
				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A 2823
				Examiner Name	Not Yet Assigned H. Lee
Sheet	4	of	12	Attorney Docket Number	M4065.1006/P1006-A

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ² -Number ³ -Kind Code ⁴ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁵
Y	BA	JP-56126916	10/1981	Akira et al.		
Y	BB	WO 97/48032	12/18/1997	Kozicki et al.		
Y	BC	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature	<i>Karen May Lee</i>	Date Considered	6/6/04
--------------------	----------------------	-----------------	--------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹Applicant's unique citation designation number (optional). ²See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO

Complete If Known**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Application Number	10/618,824
Filing Date	July 14, 2003
First Named Inventor	Terry L. Gilton
Group Art Unit	N/A 2823
Examiner Name	Not Yet Assigned H. Lee

Sheet	5	of	12	Attorney Docket Number	M4065.1006/P1006-A
-------	---	----	----	------------------------	--------------------

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
Lee	CA	Abdel-All, A.; Elshafie,A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge5As38Te57 chalcogenide glass, Vacuum 59 (2000) 845-853.	
*	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
*	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
*	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se75Ge25-xSbx, Appl. Phys. A 55 (1992) 167-169.	
*	CE	Afifi,M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe1-x, Egypt, J. Phys. 17 (1986) 335-342.	
*	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag2Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
*	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
*	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
*	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
*	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
*	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
*	CL	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: Programmable Metalization Cell/(PMC), pp. 1-6 (Pre-May 2000).	
*	CM	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.	
*	CN	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029.	
*	CO	Belin, R.; Zerouale, A.; Pradel, A.; Ribes, M., Ion dynamics in the argyrodite compound Ag7GeSe5I: non-Arrhenius behavior and complete conductivity spectra, Solid State Ionics 143 (2001) 445-455.	
*	CP	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.	
*	CQ	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag2Se-M, Thin solid films 70 (1980) L1-L4.	
*	CR	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.	
*	CS	Bernede, J.C., Switching and silver movements in Ag2Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.	
*	CT	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.	
*	CU	Bernede, J.C.; Conan, A.; Fousenan't, E.; El Bouchairi, B.; Goureaux, G., Polarized memory switching effects in Ag2Se/Se/M thin film sandwiches, Thin solid films 97 (1982) 165-171.	
Lee	CV	Bernede, J.C. et al., Transition from S- to N-type differential negative resistance in Al-Al2O3-Ag2-xSe1+x thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.	

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	6	of	12	Attorney Docket Number
-------	---	----	----	------------------------

			Complete if Known	
			Application Number	10/618,824
			Filing Date	July 14, 2003
			First Named Inventor	Terry L. Gilton
			Group Art Unit	N/A 2823
			Examiner Name	Not Yet Assigned H. Lee
Lee	CW	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg45, Solid State Ionics 70/71 (1994) 72-76.		
Lee	CX	Boolchand, P., The maximum in glass transition temperature (Tg) near x=1/3 in Ge _x Se _{1-x} Glasses, Asian Journal of Physics (2000) 9, 709-72.		
Lee	CY	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703		
Lee	CZ	Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.		
Lee	CA1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.		
Lee	CB1	Boolchand, P.; Grothaus, J.; Bresser, W.J.; Suranyi, P., Structural origin of broken chemical order in a GeSe ₂ glass, Phys. Rev. B 25 (1982) 2975-2978.		
Lee	CC1	Boolchand, P.; Grothaus, J.; Phillips, J.C., Broken chemical order and phase separation in Ge _x Se _{1-x} glasses, Solid state comm. 45 (1983) 183-185.		
Lee	CD1	Boolchand, P., Bresser, W.J., Compositional trends in glass transition temperature (Tg), network connectivity and nanoscale chemical phase separation in chalcogenides, Dept. of ECECS, Univ. Cincinnati (October 28, 1999) 45221-0030.		
Lee	CE1	Boolchand, P.; Grothaus, J., Molecular Structure of Melt-Quenched GeSe ₂ and GeS ₂ glasses compared, Proc. Int. Conf. Phys. Semicond. (Eds. Chadi and Harrison) 17 th (1985) 833-36.		
Lee	CF1	Bresser, W.; Boolchand, P.; Suranyi, P., Rigidity percolation and molecular clustering in network glasses, Phys. Rev. Lett. 56 (1986) 2493-2496.		
Lee	CG1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; de Neufville, J.P., Intrinsically broken chalcogen chemical order in stoichiometric glasses, Journal de Physique 42 (1981) C4-193-C4-196.		
Lee	CH1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; Hernandez, J.G., Molecular phase separation and cluster size in GeSe ₂ glass, Hyperfine Interactions 27 (1986) 389-392.		
Lee	CI1	Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe ₂ Crystals, Science 258 (1992) 271-274.		
Lee	CJ1	Chatterjee, R.; Asokan, S.; Titus, S.S.K., Current-controlled negative-resistance behavior and memory switching in bulk As-Te-Se glasses, J. Phys. D: Appl. Phys. 27 (1994) 2624-2627.		
Lee	CK1	Chen, C.H.; Tai, K.L., Whisker growth induced by Ag photodoping in glassy Ge _x Se _{1-x} films, Appl. Phys. Lett. 37 (1980) 1075-1077.		
Lee	CL1	Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936.		
Lee	CM1	Chen, G.; Cheng, J.; Chen, W., Effect of Si ₃ N ₄ on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.		
Lee	CN1	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.		
Lee	CO1	Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786.		
Lee	CP1	Dalven, R.; Gill, R., Electrical properties of beta-Ag ₂ Te and beta-Ag ₂ Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.		
Lee	CQ1	Davis, E.A., Semiconductors without form, Search 1 (1970) 152-155.		
Lee	CR1	Dearnaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191.		
Lee	CS1	Dejus, R.J.; Susman, S.; Volin, K.J.; Montague, D.G.; Price, D.L., Structure of Vitreous Ag-Ge-Se, J. Non-Cryst. Solids 143 (1992) 162-180.		
Lee	CT1	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.		

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	7	of	12	Attorney Docket Number	M4065.1006/P1006-A
-------	---	----	----	------------------------	--------------------

			Complete if Known		
	Application Number	10/618,824		Filing Date	July 14, 2003
	First Named Inventor	Terry L. Gilton		Group Art Unit	N/A 2823
	Examiner Name	Not Yet Assigned H. Lee			
<i>Lee</i>	CU1	Druseda, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.			
*	CV1	El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag _{2-x} Se _{1+x} /n-Si diodes, Thin Solid Films 110 (1983) 107-113.			
*	CW1	El Gharras, Z.; Bourahla, A.; Vautier, C., Role of photoinduced defects in amorphous Ge _x Se _{1-x} photoconductivity, J. Non-Cryst. Solids 155 (1993) 171-179.			
*	CX1	El Ghrandi, R.; Calas, J.; Galibert, G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273.			
*	CY1	El Ghrandi, R.; Calas, J.; Galibert, G., Ag dissolution kinetics in amorphous GeSe _{5.5} thin films from "in-situ" resistance measurements vs time, Phys. Stat. Sol. (a) 123 (1991) 451-460.			
*	CZ1	El-kady, Y.L., The threshold switching in semiconducting glass Ge ₂₁ Se ₁₇ Te ₆₂ , Indian J. Phys. 70A (1996) 507-516.			
*	CA2	Elliott, S.R., A unified mechanism for metal photodissolution in amorphous chalcogenide materials, J. Non-Cryst. Solids 130 (1991) 85-97.			
*	CB2	Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034.			
*	CC2	Elsamanoudy, M.M.; Hegab, N.A.; Fadel, M., Conduction mechanism in the pre-switching state of thin films containing Te As Ge Si, Vacuum 46 (1995) 701-707.			
*	CD2	El-Zahed, H.; El-Korashy, A., Influence of composition on the electrical and optical properties of Ge ₂₀ BixSe _{80-x} films, Thin Solid Films 376 (2000) 236-240.			
*	CE2	Fadel, M., Switching phenomenon in evaporated Se-Ge-As thin films of amorphous chalcogenide glass, Vacuum 44 (1993) 851-855.			
*	CF2	Fadel, M.; El-Shair, H.T., Electrical, thermal and optical properties of Se ₇₅ Ge ₇ Sb ₁₈ , Vacuum 43 (1992) 253-257.			
*	CG2	Feng, X.; Bresser, W.J.; Boolchand, P., Direct evidence for stiffness threshold in Chalcogenide glasses, Phys. Rev. Lett. 78 (1997) 4422-4425.			
*	CH2	Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, J. Non-Cryst. Solids 222 (1997) 137-143.			
*	CI2	Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe ₂ thin films, Phys. Rev. B 38 (1988) 12388-12403.			
*	CJ2	Fleury, G.; Hamou, A.; Viger, C.; Vautier, C., Conductivity and crystallization of amorphous selenium, Phys. Stat. Sol. (a) 64 (1981) 311-316.			
*	CK2	Fritzsche, H., Optical and electrical energy gaps in amorphous semiconductors, J. Non-Cryst. Solids 6 (1971) 49-71.			
*	CL2	Fritzsche, H., Electronic phenomena in amorphous semiconductors, Annual Review of Materials Science 2 (1972) 697-744.			
*	CM2	Gates, B.; Wu, Y.; Yin, Y.; Yang, P.; Xia, Y., Single-crystalline nanowires of Ag ₂ Se can be synthesized by templating against nanowires of trigonal Se, J. Am. Chem. Soc. (2001) currently ASAP.			
*	CN2	Gosain, D.P.; Nakamura, M.; Shimizu, T.; Suzuki, M.; Okano, S., Nonvolatile memory based on reversible phase transition phenomena in telluride glasses, Jap. J. Appl. Phys. 28 (1989) 1013-1018.			
*	CO2	Guin, J.-P.; Roux, I., T.; Kervyn, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below T _g : elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.			
*	CP2	Guin, J.-P.; Roux, I.; Sangleboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52.			
<i>Lee</i>	CQ2	Gupta, Y.P., On electrical switching and memory effects in amorphous chalcogenides, J. Non-			

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO

Complete If Known

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	8	of	12	Attorney Docket Number	M4065.1006/P1006-A
-------	---	----	----	------------------------	--------------------

		Cryst. Sol. 3 (1970) 148-154.	
<i>Lee</i>	CR2	Haberland, D.R.; Stiegler, H., New experiments on the charge-controlled switching effect in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 408-414.	
*	CS2	Haifz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses, J. Appl. Phys. 54 (1983) 1950-1954.	
*	CT2	Hajto, J.; Rose, M.J.; Osborne, I.S.; Snell, A.J.; Le Comber, P.G.; Owen, A.E., Quantization effects in metal/a-Si:H/metal devices, Int. J. Electronics 73 (1992) 911-913.	
*	CU2	Hajto, J.; Hu, J.; Snell, A.J.; Turvey, K.; Rose, M., DC and AC measurements on metal/a-Si:H/metal room temperature quantised resistance devices, J. Non-Cryst. Solids 266-269 (2000) 1058-1061.	
*	CV2	Hajto, J.; McAuley, B.; Snell, A.J.; Owen, A.E., Theory of room temperature quantized resistance effects in metal-a-Si:H-metal thin film structures, J. Non-Cryst. Solids 198-200 (1996) 825-828.	
*	CW2	Hajto, J.; Owen, A.E.; Snell, A.J.; Le Comber, P.G.; Rose, M.J., Analogue memory and ballistic electron effects in metal-amorphous silicon structures, Phil. Mag. B 63 (1991) 349-369.	
*	CX2	Hayashi, T.; Ono, Y.; Fukaya, M.; Kan, H., Polarized memory switching in amorphous Se film, Japan. J. Appl. Phys. 13 (1974) 1163-1164.	
*	CY2	Hegab, N.A.; Fadel, M.; Sedeek, K., Memory switching phenomena in thin films of chalcogenide semiconductors, Vacuum 45 (1994) 459-462.	
*	CZ2	Helbert et al., <i>Intralevel hybrid resist process with submicron capability</i> , SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 24-29 (1982).	
*	CA3	Hilt, DISSERTATION: <i>Materials characterization of Silver Chalcogenide Programmable Metallization Cells</i> , Arizona State University, pp. Title page-114 (UMI Company, May 1999).	
*	CB3	Holmquist et al., <i>Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems</i> , 62 J. AMER. CERAM. SOC., No. 3-4, pp. 183-188 (March-April 1979).	
*	CC3	Hong, K.S.; Speyer, R.F., Switching behavior in II-IV-V2 amorphous semiconductor systems, J. Non-Cryst. Solids 116 (1990) 191-200.	
*	CD3	Hosokawa, S., Atomic and electronic structures of glassy Ge _x Se _{1-x} around the stiffness threshold composition, J. Optoelectronics and Advanced Materials 3 (2001) 199-214.	
*	CE3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Constant current forming in Cr/p+a-/Si:H/V thin film devices, J. Non-Cryst. Solids 227-230 (1998) 1187-1191.	
*	CF3	Hu, J.; Hajto, J.; Snell, A.J.; Owen, A.E.; Rose, M.J., Capacitance anomaly near the metal-non-metal transition in Cr-hydrogenated amorphous Si-V thin-film devices, Phil. Mag. B 74 (1996) 37-50.	
*	CG3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Current-induced instability in Cr-p+a-/Si:H-V thin film devices, Phil. Mag. B 80 (2000) 29-43.	
*	CH3	Huggett et al., Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF ₆ , 42 Appl. Phys. Lett., No. 7, pp. 592-594 (April 1983).	
*	CI3	Iizima, S.; Sugi, M.; Kikuchi, M.; Tanaka, K., Electrical and thermal properties of semiconducting glasses As-Te-Ge, Solid State Comm. 8 (1970) 153-155.	
*	CJ3	Ishikawa, R.; Kikuchi, M., Photovoltaic study on the photo-enhanced diffusion of Ag in amorphous films of Ge ₂ S ₃ , J. Non-Cryst. Solids 35 & 36 (1980) 1061-1066.	
*	CK3	Iyetomi, H.; Vashishta, P.; Kalia, R.K., Incipient phase separation in Ag/G /Se glasses: cluster ring of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142.	
*	CL3	Jones, G.; Collins, R.A., Switching properties of thin selenium films under pulsed bias, Thin Solid Films 40 (1977) L15-L18.	
*	CM3	Joullie, A.M.; Marucchi, J., On the DC electrical conduction of amorphous As ₂ Se ₇ before switching, Phys. Stat. Sol. (a) 13 (1972) K105-K109.	
<i>Lee</i>	CN3	Joullie, A.M.; Marucchi, J., Electrical properties of the amorphous alloy As ₂ Se ₅ , Mat. Res.	

Karen May Lee 6/6/04

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Complete If Known

Application Number	10/618,824
Filing Date	July 14, 2003
First Named Inventor	Terry L. Gilton
Group Art Unit	N/A 2823
Examiner Name	Not Yet Assigned H. Lee

Sheet	9	of	12	Attorney Docket Number	M4065.1006/P1006-A
-------	---	----	----	------------------------	--------------------

		Bull. 8 (1973) 433-442.
Lee	CO3	Kaplan, T.; Adler, D., Electrothermal switching in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 538-543.
*	CP3	Kawaguchi et al., Mechanism of photosurface deposition, 164-166 J. NON-CRYST. SOLIDS, pp. 1231-1234 (1993).
*	CQ3	Kawaguchi, T.; Maruno, S.; Elliott, S.R., Optical, electrical, and structural properties of amorphous Ag-Ge-S and Ag-Ge-Se films and comparison of photoinduced and thermally induced phenomena of both systems, J. Appl. Phys. 79 (1996) 9096-9104.
*	CR3	Kawaguchi, T.; Masui, K., Analysis of change in optical transmission spectra resulting from Ag photodoping in chalcogenide film, Jpn. J. Appl. Phys. 26 (1987) 15-21.
*	CS3	Kawasaki, M.; Kawamura, J.; Nakamura, Y.; Aniya, M., Ionic conductivity of Agx(GeSe3)1-x (0=<x=<0.571) glasses, Solid state Ionics 123 (1999) 259-269.
*	CT3	Kluge, G.; Thomas, A.; Klubes, R.; Grotzschel, R., Silver photodiffusion in amorphous GeSe100-x, J. Non-Cryst. Solids 124 (1990) 186-193.
*	CU3	Kolobov, A.V., On the origin of p-type conductivity in amorphous chalcogenides, J. Non-Cryst. Solids 198-200 (1996) 728-731.
*	CV3	Kolobov, A.V., Lateral diffusion of silver in vitreous chalcogenide films, J. Non-Cryst. Solids 137-138 (1991) 1027-1030.
*	CW3	Korkinova, Ts.N.; Andreichin, R.E., Chalcogenide glass polarization and the type of contacts, J. Non-Cryst. Solids 194 (1996) 256-259.
*	CX3	Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTi chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.
*	CY3	Kozicki et al., Silver incorporation in thin films of selenium rich Ge-Se glasses, International Congress on Glass, Volume 2, Extended Abstracts, July 2001, pgs. 8-9.
*	CZ3	Michael N. Kozicki, 1. Programmable Metallization Cell Technology Description, February 18, 2000
*	CA4	Michael N. Kozicki, Axon Technologies Corp. and Arizona State University, Presentation to Micron Technology, Inc., April 6, 2000
*	CB4	Kozicki et al., Applications of Programmable Resistance Changes In Metal-Doped Chalcogenides, Electrochemical Society Proceedings, Volume 99-13, 1999, pgs. 298-309.
*	CC4	Kozicki et al., Nanoscale effects in devices based on chalcogenide solid solutions, Superlattices and Microstructures, Vol. 27, No. 516, 2000, pgs. 485-488.
*	CD4	Kozicki et al., Nanoscale phase separation in Ag-Ge-Se glasses, Microelectronic Engineering 63 (2002) pgs 155-159.
*	CE4	Lakshminarayanan, K.N.; Srivastava, K.K.; Panwar, O.S.; Dumar, A., Amorphous semiconductor devices: memory and switching mechanism, J. Instn Electronics & Telecom. Engrs 27 (1981) 16-19.
*	CF4	Lal, M.; Goyal, N., Chemical bond approach to study the memory and threshold switching chalcogenide glasses, Indian Journal of pure & appl. phys. 29 (1991) 303-304.
*	CG4	Leimer, F.; Stotzel, H.; Kottwitz, A., Isothermal electrical polarisation of amorphous GeSe films with blocking Al contacts influenced by Poole-Frenkel conduction, Phys. Stat. Sol. (a) 29 (1975) K129-K132.
*	CH4	Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GexSe1-x glass, Appl. Phys. Lett. 46 (1985) 543-545.
*	CI4	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on Se-SnO ₂ system, Jpn. J. Appl. Phys. 11 (1972) 1657-1662.
*	CJ4	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on amorphous selenium thin films, Jpn. J. Appl. Phys. 11 (1972) 606.
*	CK4	Mazurier, F.; Levy, M.; Souquet, J.L., Reversible and irreversible electrical switching in TeO ₂ -V ₂ O ₅ based glasses, Journal de Physique IV 2 (1992) C2-185 - C2-188.
Lee	CL4	McHardy et al., The dissolution of metals in amorphous chalcogenides and the eff. cts o

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Group Art Unit	N/A 2823
				Examiner Name	Not Yet Assigned H. Lee
(use as many sheets as necessary)				Attorney Docket Number	M4065.1006/P1006-A
Sheet	10	of	12		

Lee	CM4	electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)
	CN4	Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni,Bi), Mat. Chem. And Phys. 28 (1991) 253-258.
*	CO4	Mitkova, M.; Boolchand, P., Microscopic origin of the glass forming tendency in chalcogenides and constraint theory, J. Non-Cryst. Solids 240 (1998) 1-21.
*	CP4	Miyatani, S.-y., Electronic and ionic conduction in (AgxCu1-x)2Se, J. Phys. Soc. Japan 34 (1973) 423-432.
*	CQ4	Miyatani, S.-y., Electrical properties of Ag2Se, J. Phys. Soc. Japan 13 (1958) 317.
*	CR4	Miyatani, S.-y., Ionic conduction in beta-Ag2Te and beta-Ag2Se, Journal Phys. Soc. Japan 14 (1959) 996-1002.
*	CS4	Mott, N.F., Conduction in glasses containing transition metal ions, J. Non-Cryst. Solids 1 (1968) 1-17.
*	CT4	Nakayama, K.; Kitagawa, T.; Ohmura, M.; Suzuki, M., Nonvolatile memory based on phase transitions in chalcogenide thin films, Jpn. J. Appl. Phys. 32 (1993) 564-569.
*	CU4	Nakayama, K.; Kojima, K.; Hayakawa, F.; Imai, Y.; Kitagawa, A.; Suzuki, M., Submicron nonvolatile memory cell based on reversible phase transition in chalcogenide glasses, Jpn. J. Appl. Phys. 39 (2000) 6157-6161.
*	CV4	Nang, T.T.; Okuda, M.; Matsushita, T.; Yokota, S.; Suzuki, A., Electrical and optical parameters of GexSe1-x amorphous thin films, Jap. J. App. Phys. 15 (1976) 849-853.
*	CW4	Narayanan, R.A.; Asokan, S.; Kumar, A., Evidence concerning the effect of topology on electrical switching in chalcogenide network glasses, Phys. Rev. B 54 (1996) 4413-4415.
*	CX4	Neale, R.G.; Aseltine, J.A., The application of amorphous materials to computer memories, IEEE transactions on electron dev. Ed-20 (1973) 195-209.
*	CY4	Ovshinsky S.R.; Fritzsche, H., Reversible structural transformations in amorphous semiconductors for memory and logic, Metallurgical transactions 2 (1971) 641-645.
*	CZ4	Ovshinsky, S.R., Reversible electrical switching phenomena in disordered structures, Phys. Rev. Lett. 21 (1968) 1450-1453.
*	CA5	Owen, A.E.; LeComber, P.G.; Sarabayrouse, G.; Spear, W.E., New amorphous-silicon electrically programmable nonvolatile switching device, IEE Proc. 129 (1982) 51-54
*	CB5	Owen, A.E.; Firth, A.P.; Ewen, P.J.S., Photo-induced structural and physico-chemical changes in amorphous chalcogenide semiconductors, Phil. Mag. B 52 (1985) 347-362.
*	CC5	Owen, A.E.; Le Comber, P.G.; Hajto, J.; Rose, M.J.; Snell, A.J., Switching in amorphous devices, Int. J. Electronics 73 (1992) 897-906.
*	CD5	Owen et al., Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures, Nanostructure Physics and Fabrication, pp. 447-451 (M. Reed ed. 1989).
*	CE5	Pearson, A.D.; Miller, C.E., Filamentary conduction in semiconducting glass diodes, App. Phys. Lett. 14 (1969) 280-282.
*	CF5	Pinto, R.; Ramanathan, K.V., Electric field induced memory switching in thin films of the chalcogenide system Ge-As-Se, Appl. Phys. Lett. 19 (1971) 221-223.
*	CG5	Popescu, C., The effect of local non-uniformities on thermal switching and high field behavior of structures with chalcogenide glasses, Solid-state electronics 18 (1975) 671-681.
*	CH5	Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537.
*	CI5	Popov, A.I.; Geller, I.KH.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.
*	CJ5	Prakash, S.; Asokan, S.; Ghare, D.B., Easily reversible memory switching in Ge-As-Te glasses, J. Phys. D: Appl. Phys. 29 (1996) 2004-2008.
Lee	CK5	Rahman, S.; Sivarama Sastry, G., Electronic switching in Ge-Bi-Se-Te glasses, Mat. Sci. and Eng. B12 (1992) 219-222.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/618,824
(use as many sheets as necessary)				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Group Art Unit	N/A 2823
				Examiner Name	Not Yet Assigned H. Lee
Sheet	11	of	12	Attorney Docket Number	M4065.1006/P1006-A

<i>Lee</i>	CL5	Ramesh, K.; Asokan, S.; Sangunni, K.S.; Gopal, E.S.R., Electrical Switching in germanium telluride glasses doped with Cu and Ag, <i>Appl. Phys. A</i> 69 (1999) 421-425.
	CM5	Rose, M.J.; Hajto, J.; Lecomber, P.G.; Gage, S.M.; Choi, W.K.; Snell, A.J.; Owen, A.E., Amorphous silicon analogue memory devices, <i>J. Non-Cryst. Solids</i> 115 (1989) 168-170.
*	CN5	Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a-Si:H memory devices, <i>Mat. Res. Soc. Symp. Proc. V</i> 258, 1992, 1075-1080.
*	CO5	Schucocker, D.; Rieder, G., On the reliability of amorphous chalcogenide switching devices, <i>J. Non-Cryst. Solids</i> 29 (1978) 397-407.
*	CP5	Sharma, A.K.; Singh, B., Electrical conductivity measurements of evaporated selenium films in vacuum, <i>Proc. Indian Natn. Sci. Acad. A</i> , (1980) 362-368.
*	CQ5	Sharma, P., Structural, electrical and optical properties of silver selenide films, <i>Ind. J. Of pure and applied phys.</i> 35 (1997) 424-427.
*	CR5	Shimizu et al., <i>The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses</i> , 46 B. <i>CHEM SOC. JAPAN</i> , No. 12, pp. 3662-3365 (1973).
*	CS5	Snell, A.J.; Lecomber, P.G.; Hajto, J.; Rose, M.J.; Owen, A.E.; Osborne, I.L., Analogue memory effects in metal/a-Si:H/metal memory devices, <i>J. Non-Cryst. Solids</i> 137-138 (1991) 1257-1262.
*	CT5	Snell, A.J.; Hajto, J.; Rose, M.J.; Osborne, L.S.; Holmes, A.; Owen, A.E.; Gibson, R.A.G., Analogue memory effects in metal/a-Si:H/metal thin film structures, <i>Mat. Res. Soc. Symp. Proc. V</i> 297, 1993, 1017-1021.
*	CU5	Steventon, A.G., Microfilaments in amorphous chalcogenide memory devices, <i>J. Phys. D: Appl. Phys.</i> 8 (1975) L120-L122.
*	CV5	Steventon, A.G., The switching mechanisms in amorphous chalcogenide memory devices, <i>J. Non-Cryst. Solids</i> 21 (1976) 319-329.
*	CW5	Stocker, H.J., Bulk and thin film switching and memory effects in semiconducting chalcogenide glasses, <i>App. Phys. Lett.</i> 15 (1969) 55-57.
*	CX5	Tanaka, K., Ionic and mixed conduction in Ag photodoping process, <i>Mod. Phys. Lett B</i> 4 (1990) 1373-1377.
*	CY5	Tanaka, K.; Iizima, S.; Sugi, M.; Okada, Y.; Kikuchi, M., Thermal effects on switching phenomenon in chalcogenide amorphous semiconductors, <i>Solid State Comm.</i> 8 (1970) 387-389.
*	CZ5	Thomburg, D.D., Memory switching in a Type I amorphous chalcogenide, <i>J. Elect. Mat.</i> 2 (1973) 3-15.
*	CA6	Thomburg, D.D., Memory switching in amorphous arsenic triselenide, <i>J. Non-Cryst. Solids</i> 11 (1972) 113-120.
*	CB6	Thomburg, D.D.; White, R.M., Electric field enhanced phase separation and memory switching in amorphous arsenic triselenide, <i>Journal(?)</i> (1972) 4609-4612.
*	CC6	Tichy, L.; Ticha, H., Remark on the glass-forming ability in $GexSe_{1-x}$ and As_xSe_{1-x} systems, <i>J. Non-Cryst. Solids</i> 261 (2000) 277-281.
*	CD6	Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, <i>Phys. Rev. B</i> 48 (1993) 14650-14652.
*	CE6	Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, 9-13 September 1985.
*	CF6	Tregouet, Y.; Bernede, J.C., Silver movements in Ag_2Te thin films: switching and memory effects, <i>Thin Solid Films</i> 57 (1979) 49-54.
*	CG6	Uemura, O.; Kameda, Y.; Kokai, S.; Satow, T., Thermally induced crystallization of amorphous $Ge0.4Se0.6$, <i>J. Non-Cryst. Solids</i> 117-118 (1990) 219-221.
<i>Lee</i>	CH6	Uttecht, R.; Stevenson, H.; Sie, C.H.; Griener, J.D.; Raghavan, K.S., Electric field induced filament formation in As-Te-Ge glass, <i>J. Non-Cryst. Solids</i> 2 (1970) 358-370.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Examiner Signature	Kris Mai Lee	Date Considered	6/16/04
-----------------------	--------------	--------------------	---------

***EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.**

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.